VS-UFB80FA40

Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 80 A



	PRIMARY CHARACTERISTICS						
	V _R	400 V					
١ _F	$T_{(AV)}$ per module at T _C = 121 °C	80 A					
	t _{rr}	32 ns					
	Туре	Modules - diode FRED Pt®					
	Package	SOT-227					

FEATURES

- Two fully independent diodes
- Fully insulated package
- Ultrafast, soft reverse recovery, with high **RoHS** operation junction temperature (T_J max. = 175 °C)
- Low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

The VS-UFB80FA40 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V _R		400	V		
Continuous forward current per diode	I _F	T _C = 130 °C	40	А		
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	270	A .		
Maximum power dissipation per module	PD	T _C = 130 °C	90	W		
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS PER DIODE (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	400	-	-	
Forward voltage	M	I _F = 30 A	-	1.14	1.39	V
Forward voltage	V _{FM}	I _F = 30 A, T _J = 175 °C	-	0.91	1.04	
Reverse leakage current	I _{RM}	$V_{R} = V_{R}$ rated	-	-	50	μA
neverse leakage current		$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$	-	-	1	mA
Junction capacitance	CT	V _R = 200 V	-	68	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	I _F = 1.0 A, dI _F /dt = 200 A/μs, V _R = 30 V		-	32	-		
Reverse recovery time	t _{rr}	T _J = 25 °C	l _F = 30 A dl _F /dt = 200 A/μs V _R = 200 V	-	68	-	ns
		T _J = 125 °C		-	125	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	6.8	-	A nC
		T _J = 125 °C		-	15	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	215	-	
		T _J = 125 °C		-	900	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	Р		-	-	1.0	
Junction to case, both leg conducting	R _{thJC}		-	-	0.50	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			

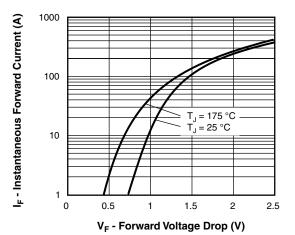
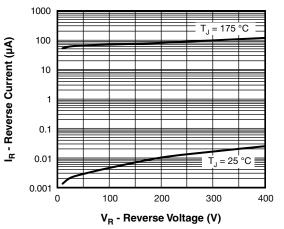
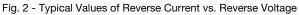
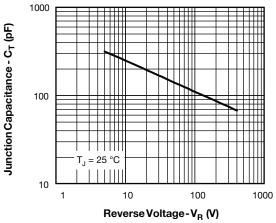
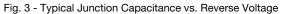


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

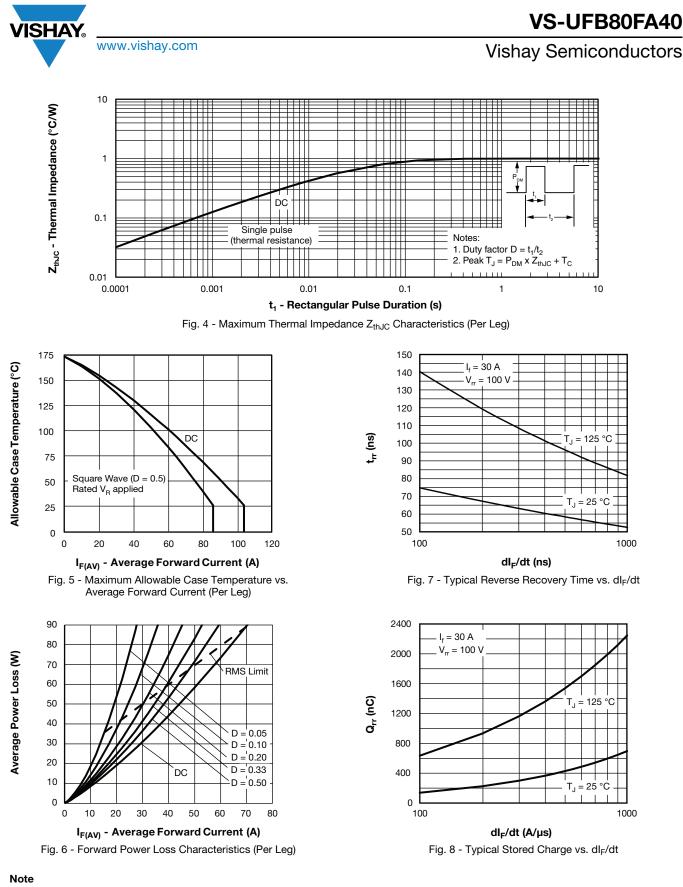








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⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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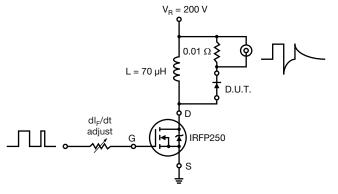
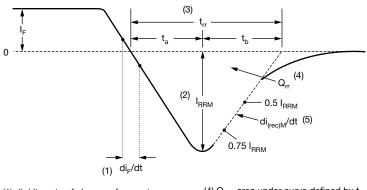


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) di_F/dt - rate of change of current through zero crossing

(4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

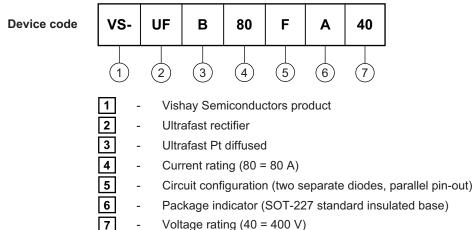
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) $di_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



Voltage rating (40 = 400 V)

CIRCUIT CONFI	CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two separate diodes, parallel pin-out	F	Lead Assignment				

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95423		
Packaging information	www.vishay.com/doc?95425		

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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